

**TECHNICAL DATA**  
**DATA SHEET D0096 REV. –**

## SILICON SCHOTTKY RECTIFIER DIE

### Applications:

- Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

### Features:

- Ultra low Reverse Leakage Current
- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Electrically / Mechanically Stable during and after Packaging

### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	$V_{RRM}$	-	30	V
Working Peak Reverse Voltage	$V_{RWM}$			
DC Blocking Voltage	$V_R$			
Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form	60	A
Peak One Cycle Non-Repetitive Surge Current	$I_{FSM}$	8.3 ms, Sine pulse <sup>(1)</sup>	860	A
Junction Temperature	$T_J$	-	-55 to +150	°C
Storage Temperature	$T_{stg}$	-	-55 to +150	°C

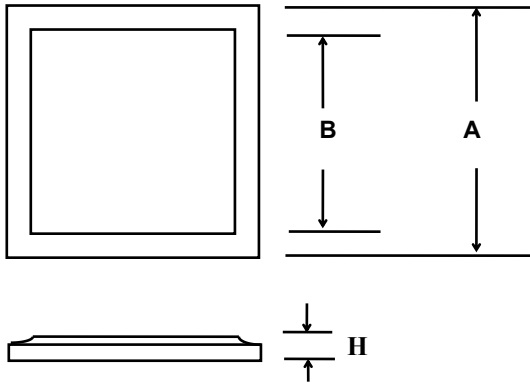
### Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop	$V_{F1}$	@ 60A, Pulse, $T_J = 25\text{ °C}$	0.53	V
	$V_{F2}$	@ 60A, Pulse, $T_J = 125\text{ °C}$	0.43	V
Reverse Current	$I_{R1}$	@ $V_R = 30V$ , Pulse, $T_J = 25\text{ °C}$	6	mA
	$I_{R2}$	@ $V_R = 30V$ , Pulse, $T_J = 125\text{ °C}$	300	mA
Junction Capacitance	$C_T$	@ $V_R = 5V$ , $T_C = 25\text{ °C}$ $f_{SIG} = 1MHz$ , $V_{SIG} = 50mV$ (p-p)	3300	pF

(1) in SHD package

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**Mechanical Dimensions: In Inches ( mm )**



Bottom side metalization Ag-5kA minimum  
 Top side metalization Ag -25kA minimum  
 Bottom side is cathode, top side is anode  
 Dimension H =0.0155±0.0005(0.39±0.013) (It can be customized according to customer requirements)

A	B
0.200 ± 0.003(5.08 ± 0.08)	0.192 ± 0.003(4.88 ± 0.08)

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